

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D T _C = +25°C
100V	80mΩ @ V _{GS} = 10V	18A
	100mΩ @ V _{GS} = 4.5V	16A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

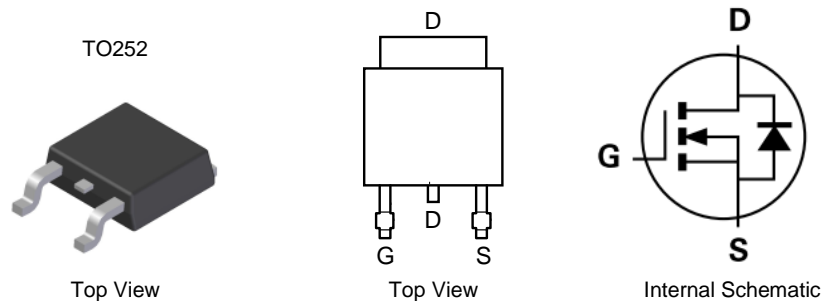
- Power Management Functions
- DC-DC Converters

Features

- Low R_{DS(ON)} – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208⁽³⁾
- Weight: 0.33 grams (Approximate)

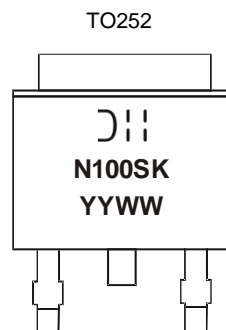


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN10H100SK3-13	TO252	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



= Manufacturer's Marking
 N100SK = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Digit of Year (ex: 14 = 2014)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	T _C = +25°C	18
		T _C = +70°C	14
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I _{DM}	16	A
Avalanche Current, L = 1mH (Note 7)	I _{AS}	8	A
Avalanche Energy, L = 1mH (Note 7)	E _{AS}	32.6	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	P _D	T _C = +25°C	37
		T _C = +70°C	24
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	46	°C/W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	3.3	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 80V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	2.0	3.0	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	65	80	mΩ	V _{GS} = 10V, I _D = 3.3A
		—	70	100		V _{GS} = 4.5V, I _D = 2A
Diode Forward Voltage	V _{SD}	—	0.77	—	V	V _{GS} = 0V, I _S = 3.2A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{ISS}	—	1172	—	pF	V _{DS} = 50V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{OSS}	—	40.8	—		
Reverse Transfer Capacitance	C _{RSS}	—	31.3	—		
Gate Resistance	R _G	—	1.6	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	25.2	—	nC	V _{DS} = 50V, I _D = 3.3A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	12.2	—		
Gate-Source Charge	Q _{gs}	—	5.3	—		
Gate-Drain Charge	Q _{gd}	—	5.9	—		
Turn-On Delay Time	t _{D(ON)}	—	5.4	—	ns	V _{DD} = 50V, R _G = 6.0Ω, I _D = 3.3A
Turn-On Rise Time	t _R	—	5.9	—		
Turn-Off Delay Time	t _{D(OFF)}	—	20	—		
Turn-Off Fall Time	t _F	—	7.3	—		
Body Diode Reverse Recovery Time	t _{RR}	—	19.7	—	ns	I _F = 3.3A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{rr}	—	15.9	—	nC	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
6. Device mounted on infinite heatsink.
7. Guaranteed by design. Not subject to product testing.
8. Short duration pulse test used to minimize self-heating effect.

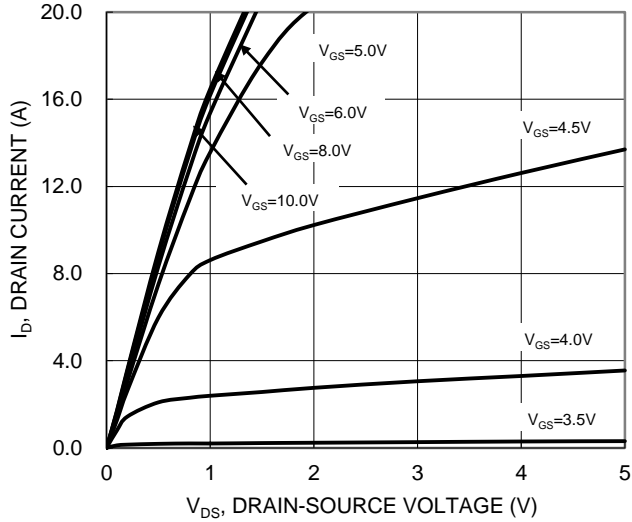


Figure 1. Typical Output Characteristic

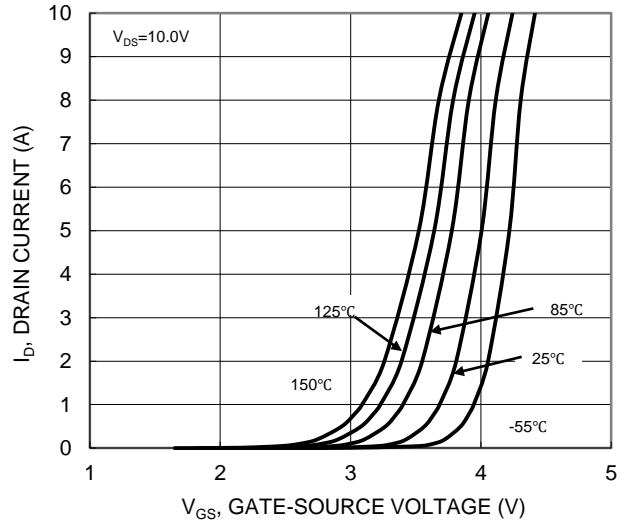


Figure 2. Typical Transfer Characteristic

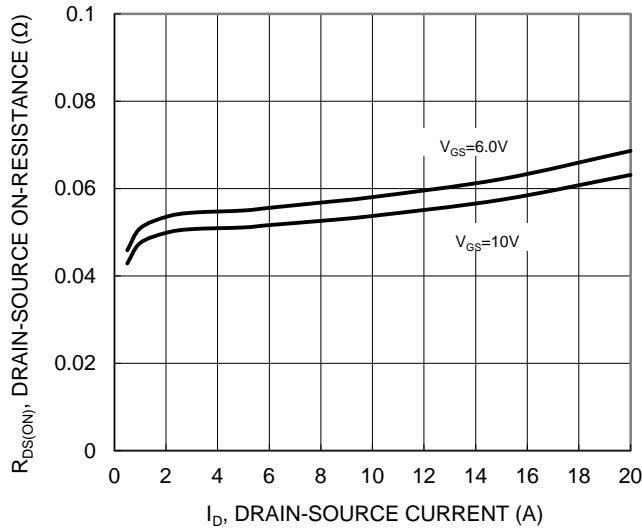


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

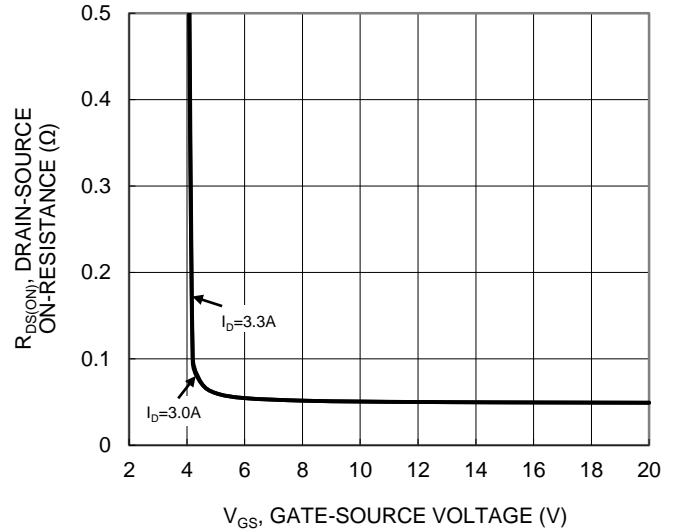


Figure 4. Typical Transfer Characteristic

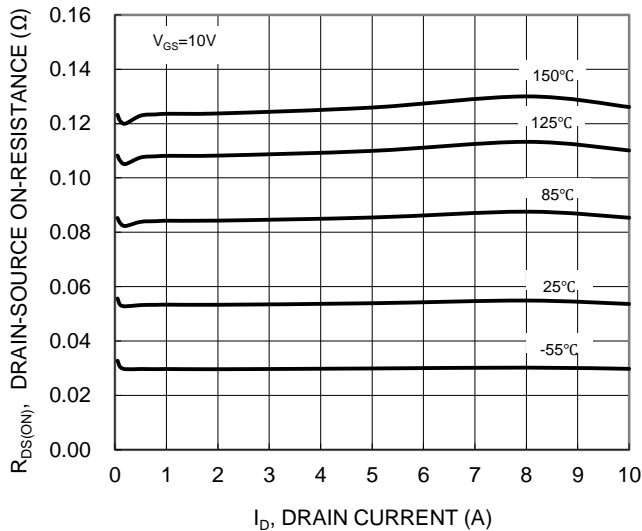


Figure 5. Typical On-Resistance vs Drain Current and Temperature

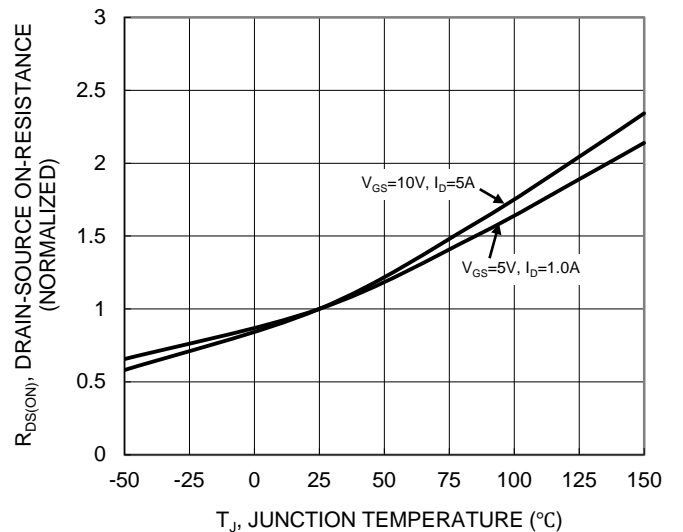


Figure 6. On-Resistance Variation with Temperature

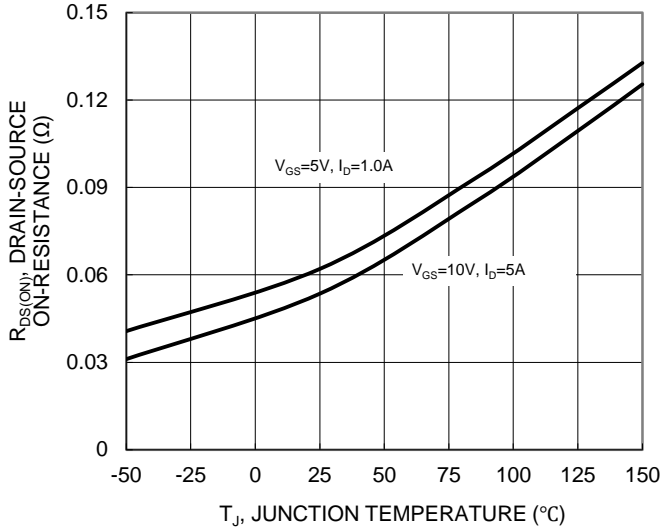


Figure 7. On-Resistance Variation with Temperature

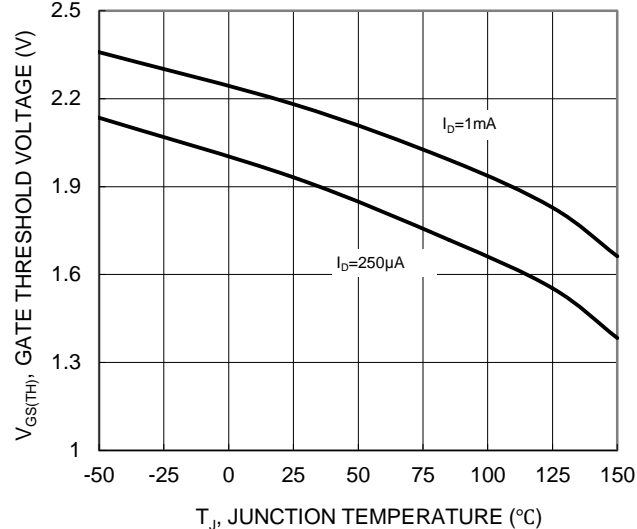


Figure 8. Gate Threshold Variation vs Temperature

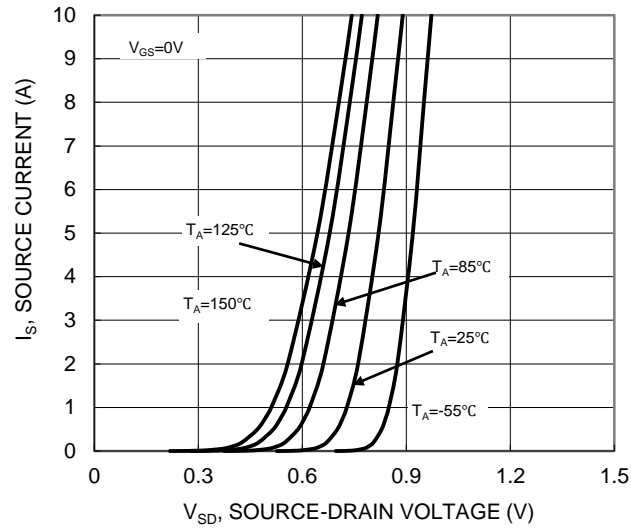


Figure 9. Diode Forward Voltage vs Current

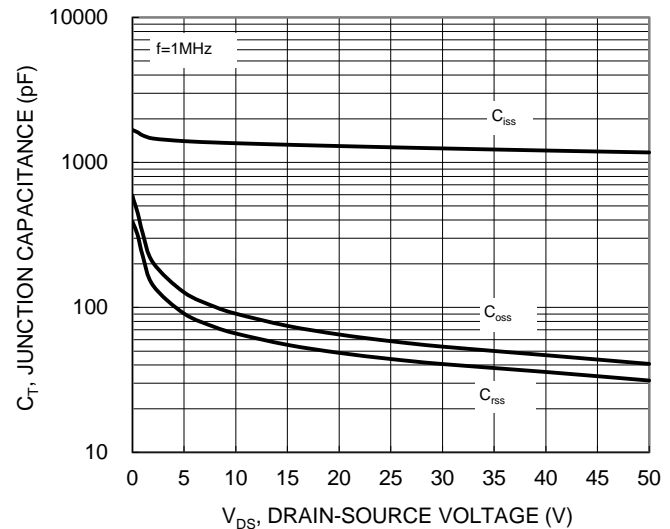


Figure 10. Typical Junction Capacitance

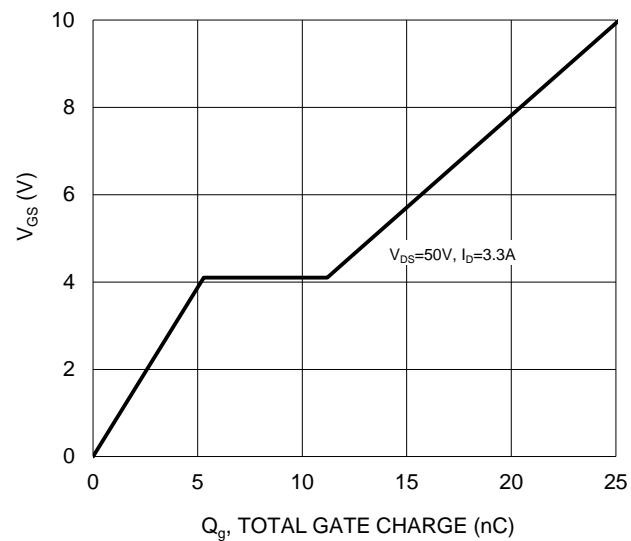


Figure 11. Gate Charge

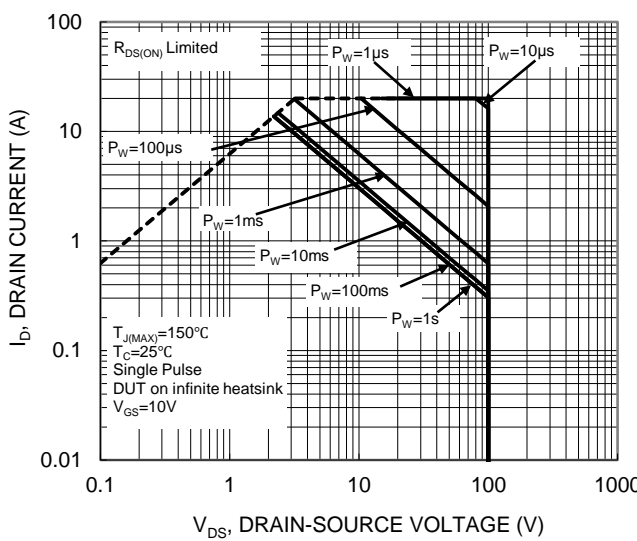


Figure 12. SOA, Safe Operation Area

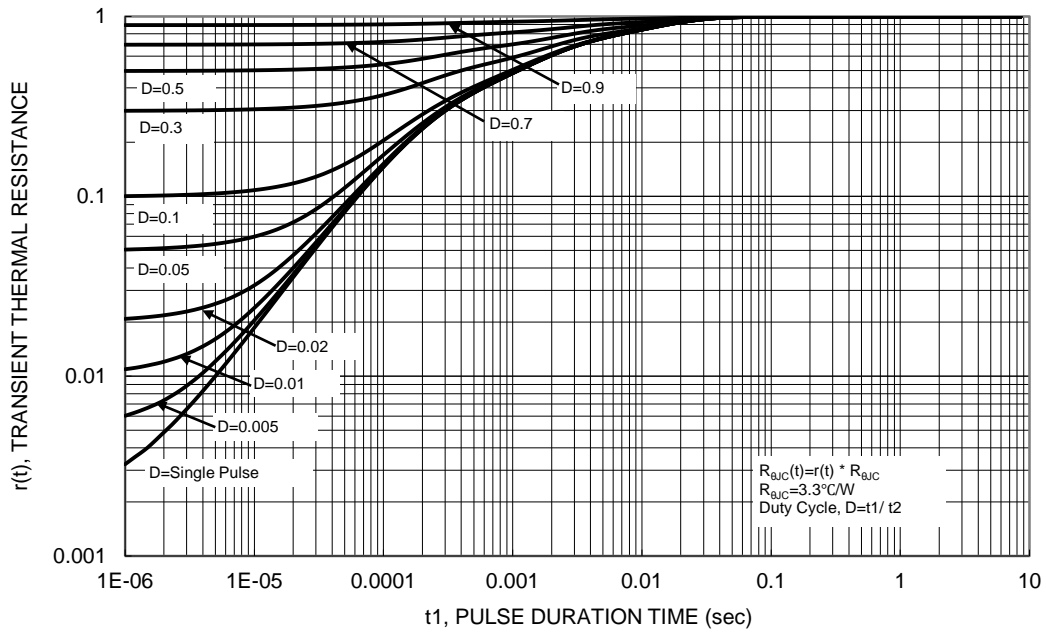
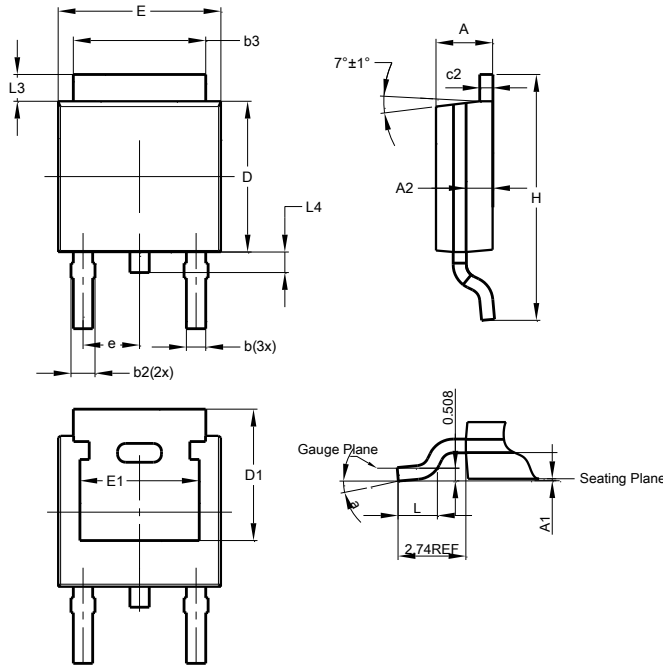


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

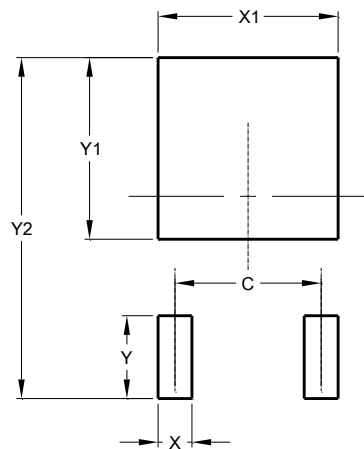
Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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